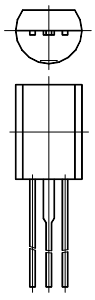
2SC2482 TRANSISTOR (NPN)

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



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FEATURE

Power dissipation

P_{CM}: 0.9 W (Tamb=25℃)

Collector current

I_{CM}: 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= 100μA , I_E=0	300		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 3 mA , I_B=0	300		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA, I_C=0	7		V
Collector cut-off current	I_{CBO}	V_{CB}= 240 V , I_E=0		1	μA
Collector cut-off current	I_{CEO}	V_{CB}= 220 V , I_B=0		5	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 7 V , I_C=0		1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=10 V, I_C= 20mA	30	150	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= 10 mA, I_B= 1 mA		1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= 10 mA, I_B= 1 mA		1	V
Transition frequency	f_T	V_{CE}= 10 V, I_C= 20mA f = 30MHz	50		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	30-90	90-150